



### **IRFB16N60LPBF Information**



For Reference Only

Part Number IRFB16N60LPBF
Manufacturer Vishay Siliconix

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

**Description** MOSFET N-CH 600V 16A TO-220AB

Package TO-220-3

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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# **IRFB16N60LPBF Specifications**

Manufacturer Part Number         IRFB16N60LPBF           Manufacturer         Vishay Siliconix           Category         Discrete Semiconductor Products           Fackage         TO-220-3           Series         -           FET Type         N-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         600V           Current - Continuous Drain (Id) @ 25°C         16A (Tc)           Drive Voltage (Max Rds On, Min Rds On)         10V           Vgs(th) (Max) @ Id         5V @ 250μA           Gate Charge (Qg) (Max) @ Vgs         100nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         2720pF @ 25V           Vgs (Max)         ±30V           FET Feature         -           Power Dissipation (Max)         310W (Tc)           Rds On (Max) @ Id, Vgs         460 mOhm @ 9A, 10V           Operating Temperature         -55°C ~ 150°C (TJ)           Mounting Type         Through Hole           Supplier Device Package         TO-220AB		
CategoryDiscrete Semiconductor ProductsPackageTO-220-3Series-FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)600VCurrent - Continuous Drain (Id) @ 25°C16A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 250μAGate Charge (Qg) (Max) @ Vgs10onC @ 10VInput Capacitance (Ciss) (Max) @ Vds2720pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)310W (Tc)Rds On (Max) @ Id, Vgs460 mOhm @ 9A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough Hole	Manufacturer Part Number	IRFB16N60LPBF
Transistors - FETs, MOSFETs - Single  Package TO-220-3  Series - FET Type N-Channel  Technology MOSFET (Metal Oxide)  Drain to Source Voltage (Vdss) 600V  Current - Continuous Drain (Id) @ 25°C 16A (Tc)  Drive Voltage (Max Rds On, Min Rds On) 10V  Vgs(th) (Max) @ Id 5V @ 250µA  Gate Charge (Qg) (Max) @ Vgs 100nC @ 10V  Input Capacitance (Ciss) (Max) @ Vds 2720pF @ 25V  Vgs (Max) +30V  FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 460 mOhm @ 9A, 10V  Operating Temperature -55°C ~ 150°C (TJ)  Mounting Type	Manufacturer	Vishay Siliconix
Package         TO-220-3           Series         -           FET Type         N-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         600V           Current - Continuous Drain (Id) @ 25°C         16A (Tc)           Drive Voltage (Max Rds On, Min Rds On)         10V           Vgs(th) (Max) @ Id         5V @ 250μA           Gate Charge (Qg) (Max) @ Vgs         100nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         2720pF @ 25V           Vgs (Max)         ±30V           FET Feature         -           Power Dissipation (Max)         310W (Tc)           Rds On (Max) @ Id, Vgs         460 mOhm @ 9A, 10V           Operating Temperature         -55°C ~ 150°C (TJ)           Mounting Type         Through Hole	Category	Discrete Semiconductor Products
Series-FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)600VCurrent - Continuous Drain (Id) @ 25°C16A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 250μAGate Charge (Qg) (Max) @ Vgs100nC @ 10VInput Capacitance (Ciss) (Max) @ Vds2720pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)310W (Tc)Rds On (Max) @ Id, Vgs460 mOhm @ 9A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough Hole		Transistors - FETs, MOSFETs - Single
FET Type  Technology  MOSFET (Metal Oxide)  Drain to Source Voltage (Vdss)  Current - Continuous Drain (Id) @ 25°C  Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Ygs (Max)  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  A60 mOhm @ 9A, 10V  Derating Temperature  MOSFET (Metal Oxide)  MOSFET (Metal Oxide)  100V  110V  110V  250µA  100nC @ 10V  110V  110	Package	TO-220-3
TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)600VCurrent - Continuous Drain (Id) @ 25°C16A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 250μAGate Charge (Qg) (Max) @ Vgs100nC @ 10VInput Capacitance (Ciss) (Max) @ Vds2720pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)310W (Tc)Rds On (Max) @ Id, Vgs460 mOhm @ 9A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough Hole	Series	-
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Vgs(th) (Max) @ Id       5V @ 250μA         Gate Charge (Qg) (Max) @ Vgs       100nC @ 10V         Input Capacitance (Ciss) (Max) @ Vds       2720pF @ 25V         Vgs (Max)       ±30V         FET Feature       -         Power Dissipation (Max)       310W (Tc)         Rds On (Max) @ Id, Vgs       460 mOhm @ 9A, 10V         Operating Temperature       -55°C ~ 150°C (TJ)         Mounting Type       Through Hole	Current - Continuous Drain (Id) @ 25°C	16A (Tc)
Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  Operating Temperature  -55°C ~ 150°C (TJ)  Mounting Type  100nC @ 10V  2720pF @ 25V  -30V  -400 mOhm @ 9A, 10V  Through Hole	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  ET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  Operating Temperature  460 mOhm @ 9A, 10V  Operating Temperature  -55°C ~ 150°C (TJ)  Mounting Type  Through Hole	Vgs(th) (Max) @ Id	5V @ 250μA
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Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  460 mOhm @ 9A, 10V  Operating Temperature  -55°C ~ 150°C (TJ)  Mounting Type  Through Hole	Vgs (Max)	±30V
Rds On (Max) @ Id, Vgs460 mOhm @ 9A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough Hole	FET Feature	-
Operating Temperature -55°C ~ 150°C (TJ)  Mounting Type Through Hole	Power Dissipation (Max)	310W (Tc)
Mounting Type Through Hole	Rds On (Max) @ Id, Vgs	460 mOhm @ 9A, 10V
	Operating Temperature	-55°C ~ 150°C (TJ)
Supplier Device Package TO-220AB	Mounting Type	Through Hole
	Supplier Device Package	TO-220AB
Package / Case TO-220-3	Package / Case	TO-220-3
Report errors?		Report errors?

#### **IRFB16N60LPBF** Guarantees



#### **Quality Guarantees**

We provide 90 days warranty. \*

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



#### **Service Guarantees**

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

### **IRFB16N60LPBF Payment Methods**



















## **IRFB16N60LPBF Shipping Methods**













If you have any question about IRFB16N60LPBF, please do not hesitate to contact us!

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